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Sheet 1 of 2

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	APPLICANT Tsong, et al.	
	FILING DATE October 16, 2001	GROUP 1765

U.S. PATENT DOCUMENTS

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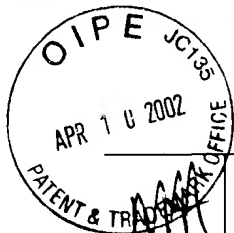
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FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
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OTHER DOCUMENTS (Including Author, Title, Date Pertinent Pages, Etc.)

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Matthew Anderson

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